

C3M0120065L-TR-VB Datasheet

N-Channel 650V (D-S) SiC Power MOSFET

PRODUCT SUMMARY

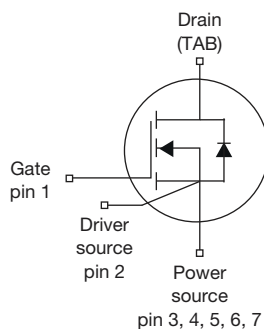
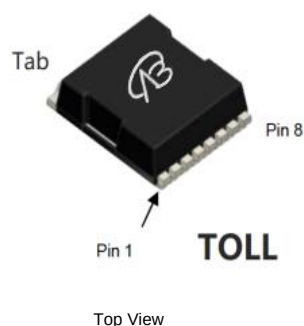
V_{DS} (V)	650	
$R_{DS(on)}$ at 25 °C (Ω)	$V_{GS} = 18$ V	0.055
Q_g (nC)	40	

FEATURES

- Low figure-of-merit (FOM) $R_{on} \times Q_g$
- Higher robustness and system reliability
- Kelvin source provides up to 4 times lower switching losses
- Ultra low gate charge (Q_g)
- Avalanche energy rated (UIS)

APPLICATIONS

- Server and telecom power supplies
- EV charging infrastructure
- Solar PV inverters
- DC/DC converter



ABSOLUTE MAXIMUM RATINGS ($T_C = 25$ °C, unless otherwise noted)

PARAMETER			SYMBOL	LIMIT	UNIT
Drain-Source Voltage			V _{DS}	650	V
Gate-Source Voltage			V _{GS}	-10 / +22	
Continuous Drain Current (T _J = 175 °C)	V _{GS} at 18 V	T _C = 25 °C	I _D	35	A
		T _C = 100 °C		25	
Pulsed Drain Current ^a			I _{DM}	95	
Linear Derating Factor				2.1	W/°C
Single Pulse Avalanche Energy ^b			E _{AS}	160	mJ
Maximum Power Dissipation			P _D	192	W
Operating Junction and Storage Temperature Range			T _J , T _{stg}	-55 to +175	°C
Drain-Source Voltage Slope	T _J = 125 °C		dV/dt	150	V/ns
Reverse Diode dV/dt ^d		100			
Soldering Recommendations (Peak Temperature) ^c	for 10 s			260	°C

Notes

- Repetitive rating; pulse width limited by maximum junction temperature.
- $V_{DD} = 50$ V, starting $T_J = 25$ °C, $L = 1$ mH, $R_g = 25$ Ω .
- 1.6 mm from case.
- $I_{SD} \leq I_D$, $dI/dt = 100$ A/ μ s, starting $T_J = 25$ °C.

THERMAL RESISTANCE RATINGS

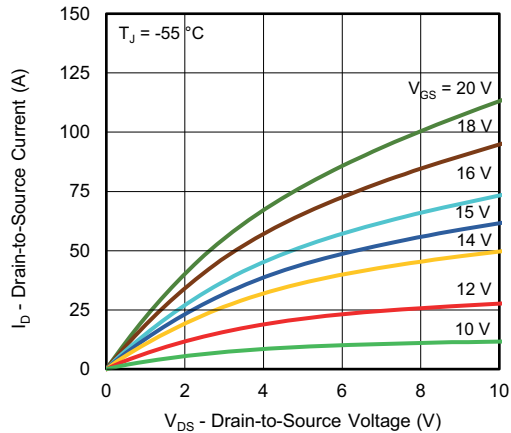
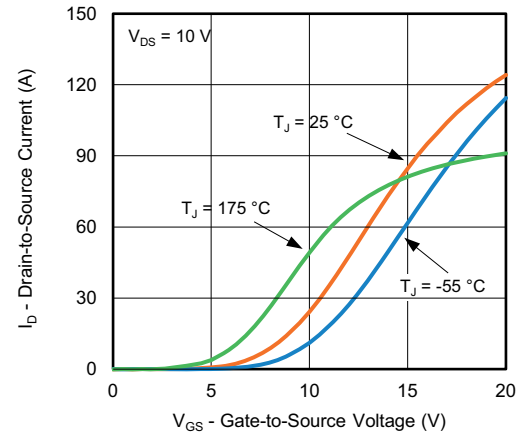
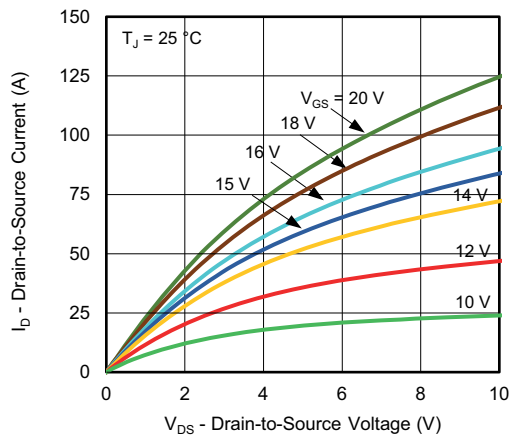
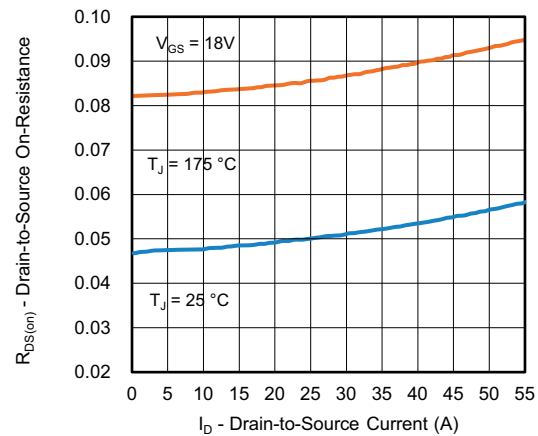
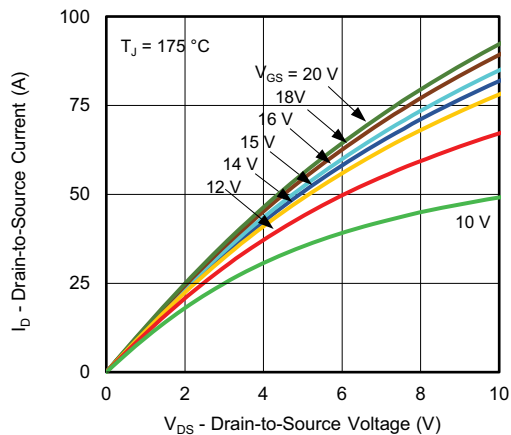
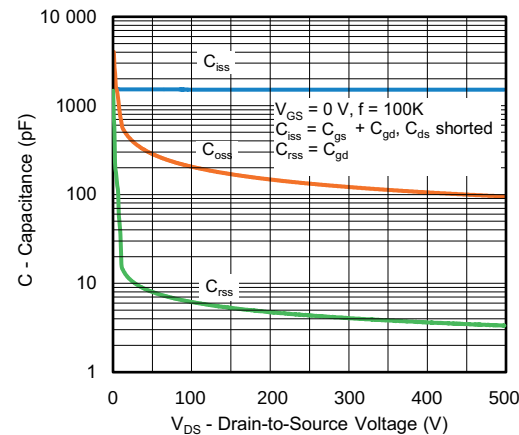
PARAMETER	SYMBOL	TYP.	MAX.	UNIT
Maximum Junction-to-Ambient	R_{thJA}	-	62	°C/W
Maximum Junction-to-Case (Drain)	R_{thJC}	-	0.78	

SPECIFICATIONS ($T_J = 25\text{ °C}$, unless otherwise noted)

PARAMETER	SYMBOL	TEST CONDITIONS		MIN.	TYP.	MAX.	UNIT
Static							
Drain-Source Breakdown Voltage	V _{DS}	V _{GS} = 0 V, I _D = 1 mA		650	-	-	V
V _{DS} Temperature Coefficient	ΔV _{DS} /T _J	Reference to 25 °C, I _D = 1 mA		-	0.70	-	V/°C
Gate-Source Threshold Voltage (N)	V _{GS(th)}	V _{DS} = V _{GS} , I _D = 5 mA		2	-	4.5	V
Gate-Source Leakage	I _{GSS}	V _{GS} = +18 V		-	-	100	nA
		V _{GS} = - 8 V		-	-	100	nA
Zero Gate Voltage Drain Current	I _{DSS}	V _{DS} = 650V, V _{GS} = 0 V		-	10	-	μA
		V _{DS} = 650 V, V _{GS} = 0 V, T _J = 125 °C		-	-	100	
Drain-Source On-State Resistance	R _{DS(on)}	V _{GS} = 18 V	I _D = 20A	-	0.055	-	Ω
Forward Transconductance	g _{fs}	V _{DS} = 0 V, I _D = 20 A		-	10	-	S
Dynamic							
Input Capacitance	C _{iss}	V _{GS} = 0 V, V _{DS} = 600 V, f = 100 KHz		-	1500	-	pF
Output Capacitance	C _{oss}			-	90	-	
Reverse Transfer Capacitance	C _{rss}			-	3	-	
Effective Output Capacitance, Energy Related ^a	C _{o(er)}	V _{DS} = 0 V to 400 V, V _{GS} = 0 V		-	120	-	
Effective Output Capacitance, Time Related ^b	C _{o(tr)}			-	160	-	
Total Gate Charge	Q _g	V _{GS} = -5/18 V	I _D = 20 A, V _{DS} = 400 V	-	40	-	nC
Gate-Source Charge	Q _{gs}			-	20	-	
Gate-Drain Charge	Q _{gd}			-	23	-	
Turn-On Delay Time	t _{d(on)}	V _{DD} = 400 V, I _D =20A V _{GS} = -5/15 V		-	12	15	ns
Rise Time	t _r			-	10	13	
Turn-Off Delay Time	t _{d(off)}			-	20	-	
Fall Time	t _f			-	10	-	
Gate Input Resistance	R _g	f = 1 MHz, open drain		-	8.2	-	Ω
Drain-Source Body Diode Characteristics							
Continuous Source-Drain Diode Current	I _S	MOSFET symbol showing the integral reverse p - n junction diode 		-	-	30	A
Pulsed Diode Forward Current	I _{SM}			-	-	90	
Diode Forward Voltage	V _{SD}	T _J = 25 °C, I _S = 20 A, V _{GS} = 0		-	-	4.1	V
Reverse Recovery Time	t _{rr}	T _J = 25 °C, I _F = I _S = 20 A, dI/dt = 1000 A/μs, V _R = 400 V		-	12	-	ns
Reverse Recovery Charge	Q _{rr}			-	0.06	-	μC
Reverse Recovery Current	I _{RRM}			-	10	-	A

Notes

- a. $C_{oss(er)}$ is a fixed capacitance that gives the same energy as C_{oss} while V_{DS} is rising from 0 % to 60 % V_{DSS} .
 b. $C_{oss(tr)}$ is a fixed capacitance that gives the same charging time as C_{oss} while V_{DS} is rising from 0 % to 60 % V_{DSS} .

TYPICAL CHARACTERISTICS (25 °C, unless otherwise noted)**Fig. 1 - Typical Output Characteristics****Fig. 4 - Typical Transfer Characteristics****Fig. 2 - Typical Output Characteristics****Fig. 5 - Normalized On-Resistance vs. Drain Current****Fig. 3 - Typical Output Characteristics****Fig. 6 - Typical Capacitance vs. Drain-to-Source Voltage**

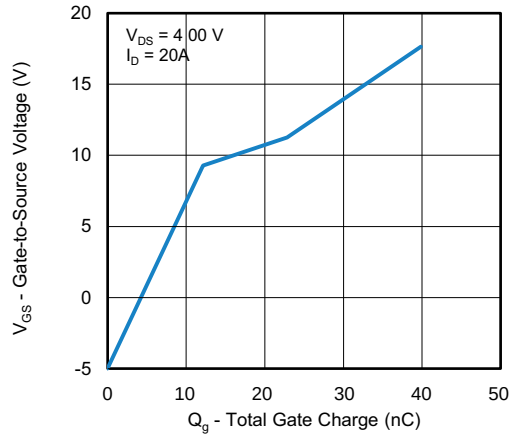


Fig. 7 - Typical Gate Charge vs. Gate-to-Source Voltage

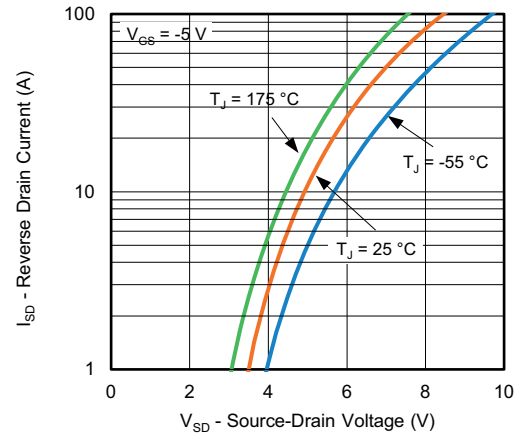


Fig. 10 - Typical Source-Drain Diode Forward Voltage

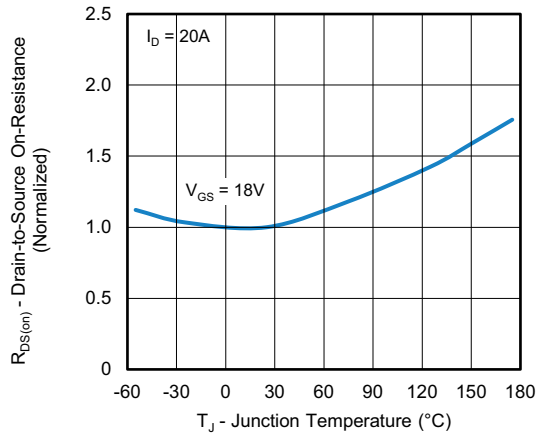


Fig. 8 - Normalized On-Resistance vs. Temperature

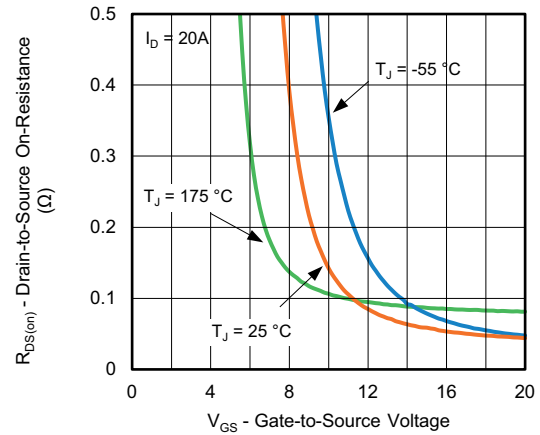


Fig. 11 - On-Resistance vs. Gate-to-Source Voltage

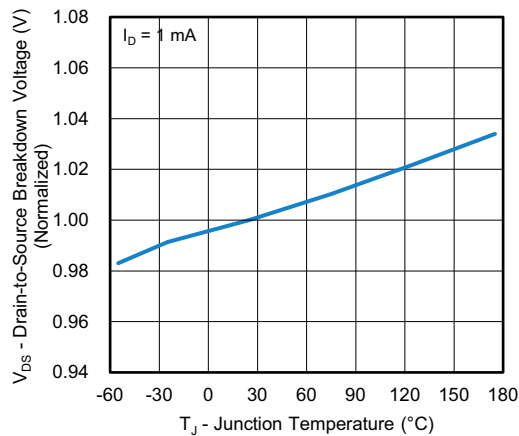


Fig. 9 - Drain-to-Source Voltage vs. Temperature

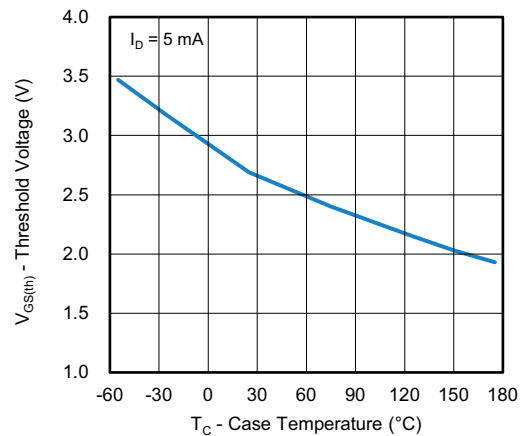


Fig. 12 - Threshold Voltage vs. Case Temperature

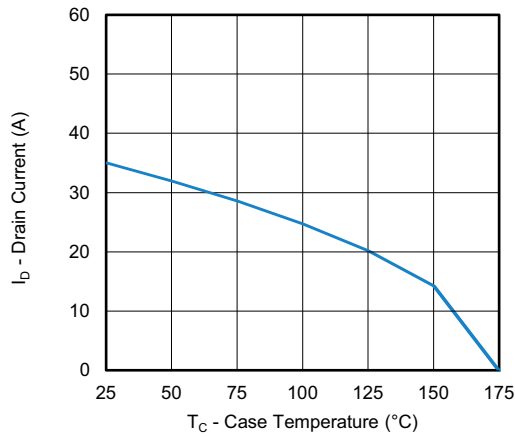


Fig. 13 - Drain Current vs. Case Temperature

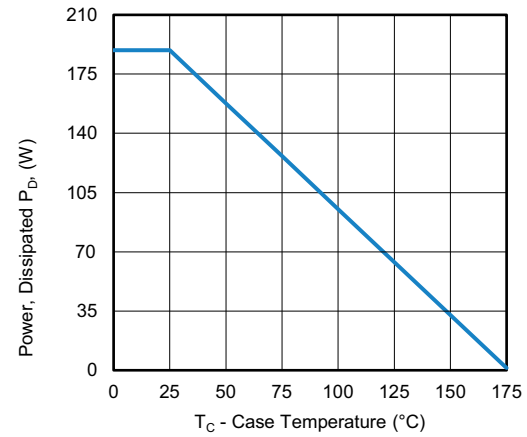
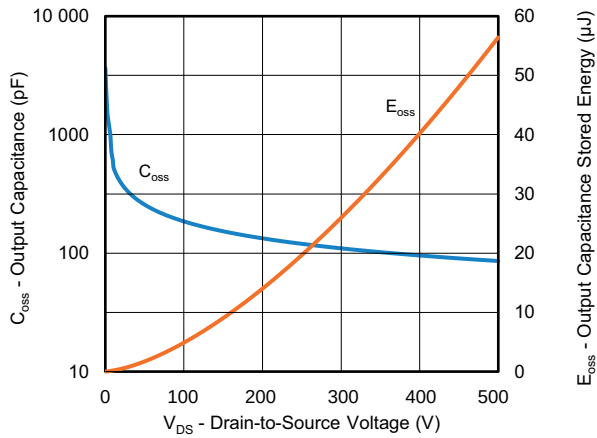
Fig. 15 - Power, Dissipated P_D vs. Case Temperature

Fig. 14 - Output Capacitance and its Stored Energy vs. Drain-to-Source Voltage

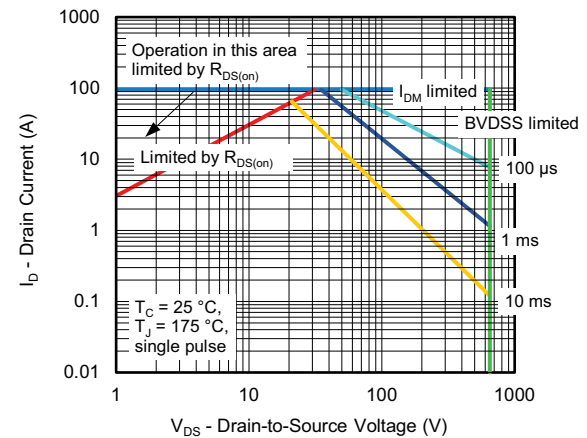


Fig. 16 - Safe Operating Area

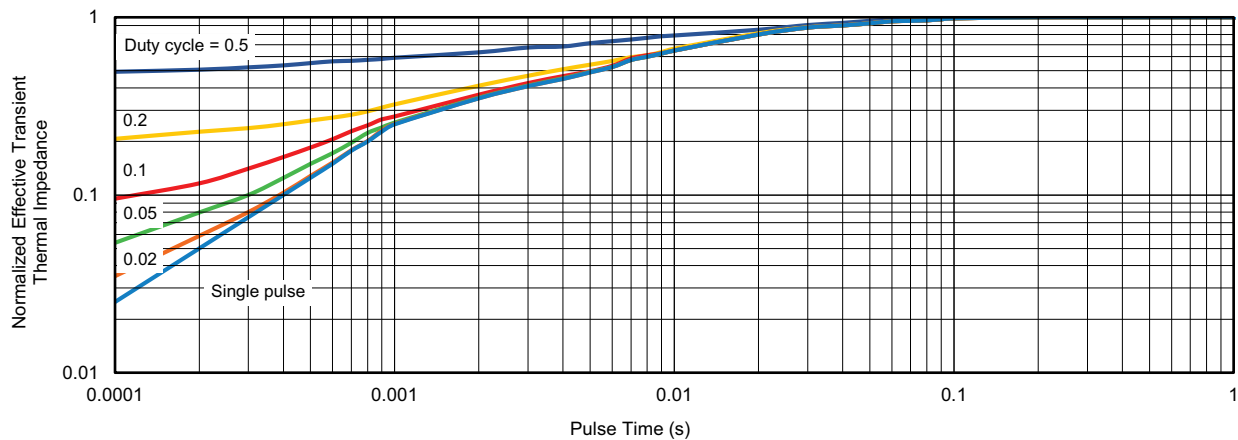


Fig. 17 - Transient Thermal Impedance

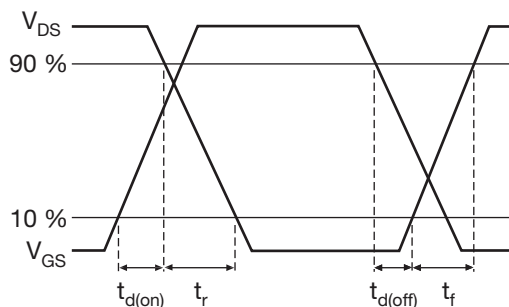


Fig. 18 - Waveforms of Switching Time

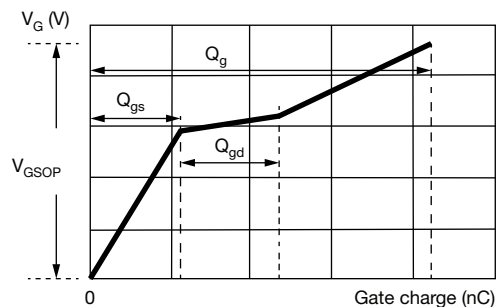


Fig. 21 - Waveforms for Gate Charge

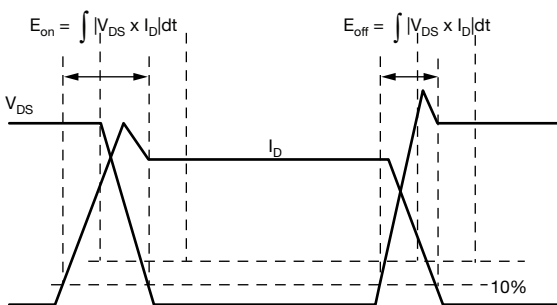


Fig. 19 - Waveforms for Switching Energy

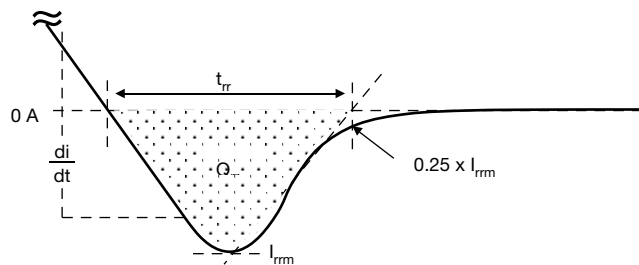


Fig. 22 - Waveforms for Reverse Recovery

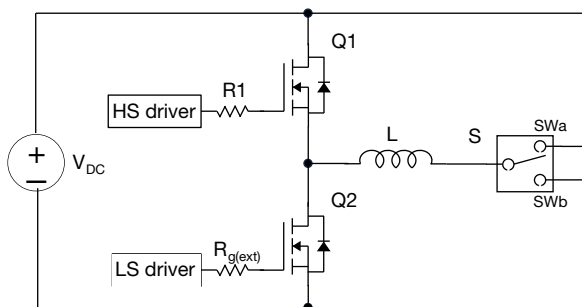


Fig. 20 - Switching and Reverse Diode Characteristics Measurement Circuit

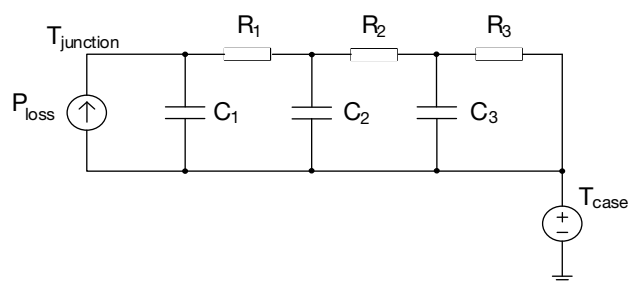
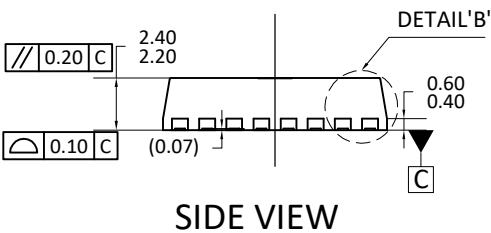
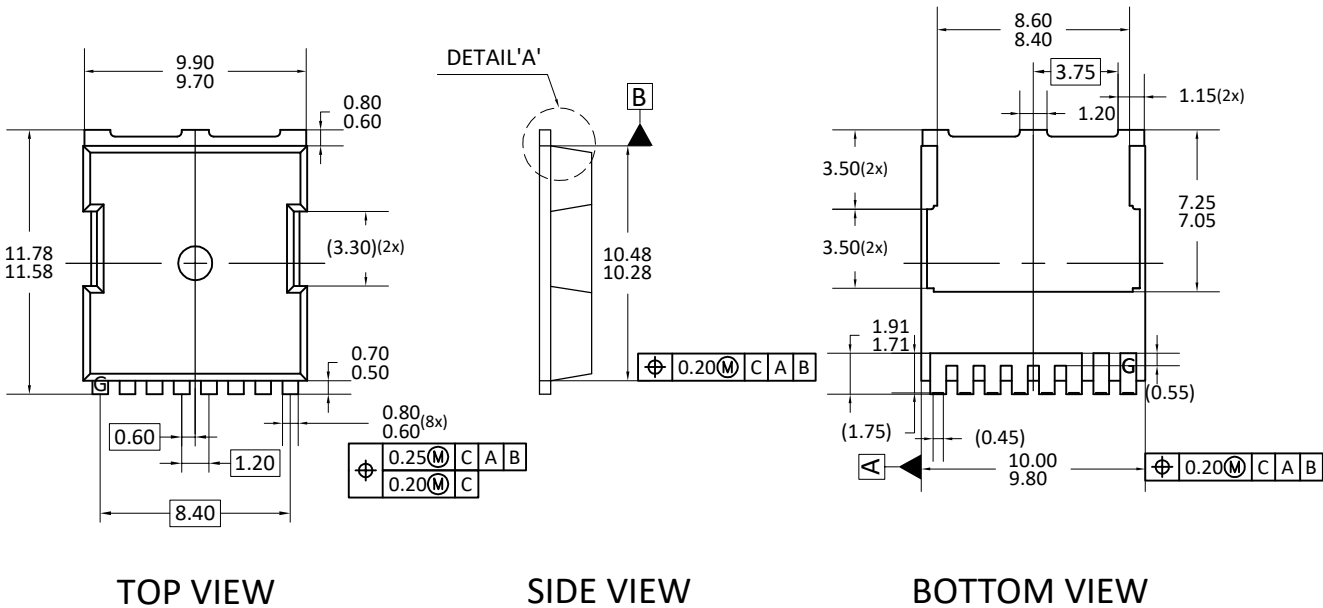


Fig. 23 - Thermal Equivalent Circuit

TOLL PACKAGE OUTLINE



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